Abstracts

An Improved GaAs MESFET Model for the Pulsed I-V Measurement

K. Fujii. "An Improved GaAs MESFET Model for the Pulsed I-V Measurement." 1995 MTT-S International Microwave Symposium Digest 95.2 (1995 Vol. II [MWSYM]): 615-618.

This paper describes an improved large signal model of the GaAs MESFET that agrees accurately with the I-V characteristics produced by the pulsed I-V measurement of the GaAs MESFET. The pulsed I-V measurement system developed and used to evaluate the performance of the model is also described. The calculated results for a microwave power amplifier predicted using an improved large signal model show good agreement with the experimental results obtained using the pulsed I-V measurement system.

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